

Anomalous Hall effect in anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ at low temperature regime

K. Ueno,^{1, a} T. Fukumura,¹ H. Toyosaki,¹ M. Nakano,¹ and M. Kawasaki^{1,2}

¹Institute for Materials Research, Tohoku University, Sendai 980-8577, Japan

²CREST, Japan Science and Technology Agency (JST), Kawaguchi 332-0012, Japan

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Anomalous Hall effect (AHE) of a ferromagnetic semiconductor anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ thin film is studied from 10 K to 300 K. Magnetic field dependence of anomalous Hall resistance is coincident with that of magnetization, while the anomalous Hall resistance decreases at low temperature in spite of nearly temperature-independent magnetization. Anomalous Hall conductivity σ_{AHE} is found to be proportional to the square of Hall mobility, suggesting that charge scattering strongly affects the AHE in this system. The anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ also follows a scaling relationship to conductivity σ_{xx} as $\sigma_{\text{AHE}} \propto \sigma_{xx}^{1.6}$, which was observed for another polymorph rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$, suggesting an identical mechanism of their AHE.

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Anomalous Hall effect (AHE) commonly observed for ferromagnetic metals is a good measure of magnetic ordering for thin film specimen and also is an important physical quantity for semiconductor spintronics devices such as field-effect transistor.(1; 2) Both anatase and rutile phases $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ are one of the most promising candidates for future spintronics devices because of their room temperature ferromagnetism.(3; 4) For rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$, systematic variation in AHE was observed as functions of x and charge density, representing typical characteristics of ferromagnetic semiconductors.(5) Also, the magnetic tunneling junction has already been realized to show tunneling magnetoresistance up to 200 K.(6) For a field-effect switching of ferromagnetism, anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ is more appropriate than rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ because ferromagnetism appears at lower charge density for the former, making the field effect switching easier. However, there has been only a few studies reported for AHE of anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$.(7; 8; 9) Therefore, detailed studies on AHE with comparing other ferromagnetic semiconductors are necessary in order to elucidate validity of field effect applications. In addition, AHE itself is currently investigated both theoretically and experimentally since detail mechanism of AHE has not been clear so far.(10; 11)

Here, we report on the AHE of an anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ thin film at low temperature regime, focusing on dependence of AHE on electric transport properties and magnetization. Particularly, scaling relationship between anomalous Hall conductivity and conductivity for anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ is compared with another polymorph rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$.

The anatase $\text{Ti}_{0.95}\text{Co}_{0.05}\text{O}_{2-\delta}$ film (40 nm) was grown on (001) LaAlO_3 single crystal substrate by pulsed laser deposition with KrF excimer laser in 10^{-6} Torr of oxygen at 400°C after the deposition of TiO_2 buffer layer (5 nm) in 10^{-3} Torr of oxygen at 650°C . The reflection high-energy electron diffraction intensity was monitored *in situ* during the film growth, and the intensity oscillation was observed during the initial stage of growth up to 15 nm of the $\text{Ti}_{0.95}\text{Co}_{0.05}\text{O}_{2-\delta}$ layer. The

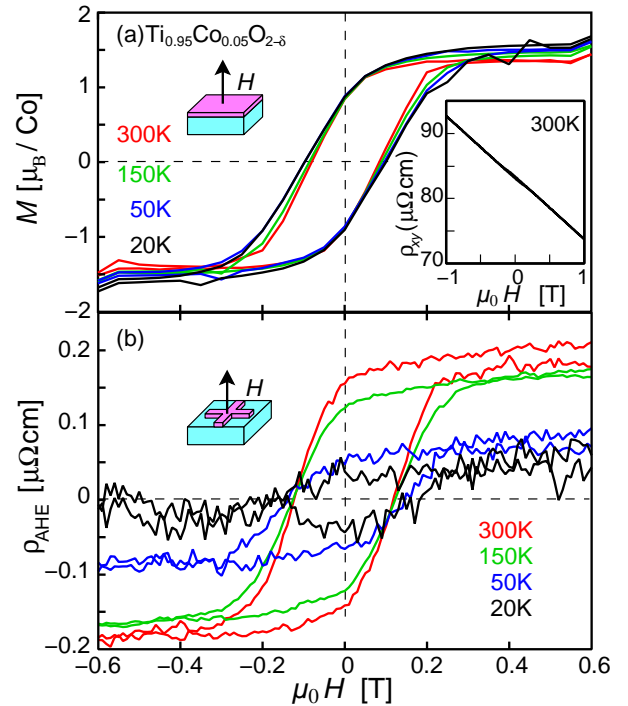


FIG. 1 Magnetic field H dependence of (a) magnetization M and (b) anomalous Hall resistivity ρ_{AHE} of an anatase $\text{Ti}_{0.95}\text{Co}_{0.05}\text{O}_{2-\delta}$ film at various temperatures. Inset in (a) is H dependence of transverse Hall resistivity ρ_{xy} at 300 K.

deposited film was divided into two pieces. One was used for magnetization measurements where the magnetization data of the film was deduced from the measured magnetization data by subtracting the diamagnetic background of the LaAlO_3 substrate. Another was photolithographically patterned into Hall bars with a channel of $200\mu\text{m}$ long \times $60\mu\text{m}$ wide for transport measurements.

Figure 1 (a) shows magnetic field H dependence of the magnetization M at various temperatures. M is almost temperature independent and saturated above 0.5 T. Inset of Fig. 1 shows H dependence of transverse Hall resistivity ρ_{xy} at

^aElectronic mail: uenok@imr.tohoku.ac.jp

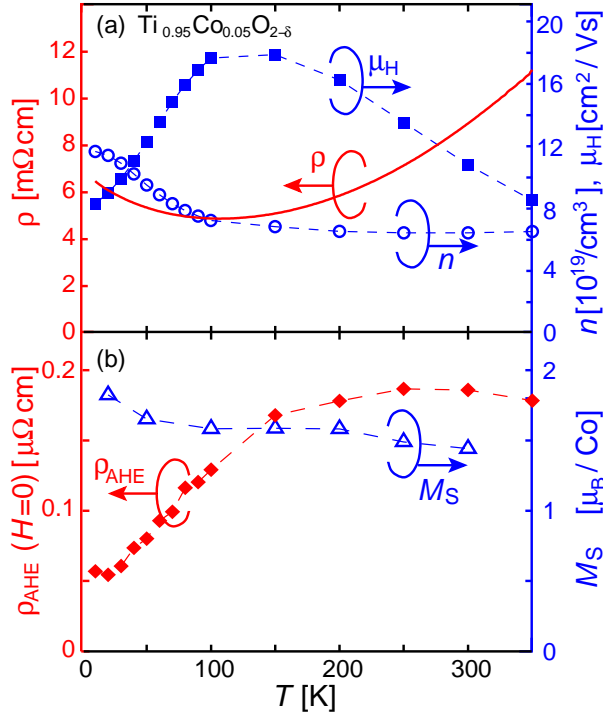


FIG. 2 (a) Temperature dependence of resistivity ρ (solid line), charge density n (\circ) and Hall mobility μ_H (\blacksquare) for the same film as in Fig. 1. (b) Temperature dependence of anomalous Hall resistivity ρ_{AHE} (\blacklozenge) for $\mu_0 H = 0$ T and saturation magnetization M_S (\triangle) for $\mu_0 H = 1$ T extracted from Fig. 1.

300 K. In ferromagnetic metals, ρ_{xy} is the sum of ordinary and anomalous parts of Hall resistivity. The former is expressed as $R_0 H$, where R_0 is ordinary Hall coefficient which is inversely proportional to charge density n and used to evaluate the Hall mobility μ_H . The latter ρ_{AHE} is supposed to be proportional to M . In this study, $R_0 H$ was deduced from the slope of ρ_{xy} vs. H curves for $|\mu_0 H| > 0.5$ T, while ρ_{AHE} was deduced by subtracting $R_0 H$ from ρ_{xy} . Figure 1 (b) shows H dependence of ρ_{AHE} at various temperatures. ρ_{AHE} vs. H curves are mostly coincident with M vs. H curves representing that $\rho_{\text{AHE}}(H)$ is proportional to $M(H)$. (12) By a close look, H dependence of ρ_{AHE} around the coercive field is appeared to be steeper than that of M . Similar difference between ρ_{AHE} vs. H and M vs. H curves has been often observed in other ferromagnetic semiconductors such as (Ga,Mn)As.(13)

Next, we will discuss the temperature dependence of electric properties in detail. Figure 2(a) shows temperature dependence of ρ , n and μ_H . The film shows n -type and metallic ρ down to 100 K with a slight upturn of ρ at lower temperature, in contrast to semiconducting behavior in rutile film having similar value of ρ . This is because anatase has higher μ_H reaching to $10 \text{ cm}^2/\text{Vs}$ at room temperature in contrast with that of rutile ($0.1 \text{ cm}^2/\text{Vs}$). μ_H increases with decreasing temperature down to 150 K following $T^{-3/2}$ law, presumably due to phonon scattering mechanism. At lower temperature, μ_H rapidly decreases with decreasing temperature, presumably due to magnetic and/or ionized impurity scattering by Co ions

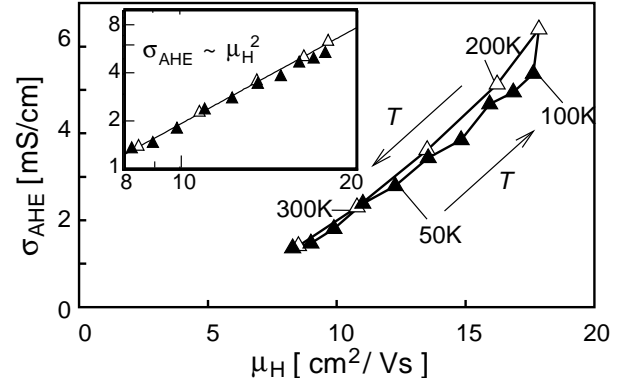


FIG. 3 Hall mobility μ_H dependence of anomalous Hall conductivity σ_{AHE} . σ_{AHE} is deduced from ρ_{AHE} and ρ values in Fig. 2 by using the relationship $\sigma_{\text{AHE}} \approx \rho_{\text{AHE}}/\rho_{xx}^2$ (see text). Higher (≥ 150 K) and lower (≤ 100 K) temperature data are represented by open and solid symbols, respectively, for convenience. The inset is a log-log plot of the σ_{AHE} vs. μ_H curve.

and oxygen vacancies. In contrast, n is almost temperature independent down to 100 K followed by a slight increase with decreasing temperature without carrier freeze-out effect down to 2 K. The temperature dependence of n indicates the charge conduction in metallic impurity band in this system as is commonly observed in SrTiO₃ single crystals.(14) The increase of n might be originated from the increased permittivity at low temperature like rutile TiO₂,(15) as is observed in reduced SrTiO₃.(14)

As shown in Fig. 2 (b), saturation magnetization M_S is nearly temperature independent, whereas ρ_{AHE} decreases rapidly below 150 K with decreasing temperature, hence $\rho_{\text{AHE}}(T)$ is not proportional to $M(T)$. Such temperature variation of ρ_{AHE} is related with that of transport properties in Fig. 2 (a). In group III-V ferromagnetic semiconductors, Hall conductivity ($\sigma_{xy} \equiv \rho_{xy}/(\rho_{xx}^2 + \rho_{yy}^2)$) is known to be an essential measure of the strength of AHE, in which ordinary Hall term is negligible. In this study, σ_{xy} is approximated to be $\rho_{xy}/\rho_{xx}^2 = R_0 H/\rho_{xx}^2 + \rho_{\text{AHE}}/\rho_{xx}^2$ since $\rho_{xy} \sim \rho_{xx}/10^3$. Thus, we can simplify the anomalous Hall conductivity σ_{AHE} as $\rho_{\text{AHE}}/\rho_{xx}^2$. Figure 3 shows the μ_H dependence of σ_{AHE} at various temperatures obtained from the data in Fig. 2. It appears that σ_{AHE} has good one-to-one correspondence to μ_H , irrespective of temperature ranges where μ_H is limited by the phonon and impurity scattering at higher and lower temperatures than 150 K, respectively. As shown in inset of Fig. 3, σ_{AHE} is proportional to μ_H^2 . For single band conduction model, μ_H is expressed as $e\tau/m^*$ (e : electron charge, m^* : effective mass and τ : scattering time) where τ is temperature dependent parameter governed by various charge scattering mechanisms. Taking the constant m^* into account, σ_{AHE} can be connected with τ regardless of the scattering mechanism.

Let us examine the observed AHE together with the other ferromagnetic semiconductors. For group III-V ferromagnetic semiconductors, σ_{AHE} is theoretically expressed as a function of conductivity σ_{xx}^α , where the exponent α reflects the origin of AHE such as skew scattering and side-jump mechanisms (corresponding to $\alpha \approx 1$ and ≈ 0 , respectively).(10) On

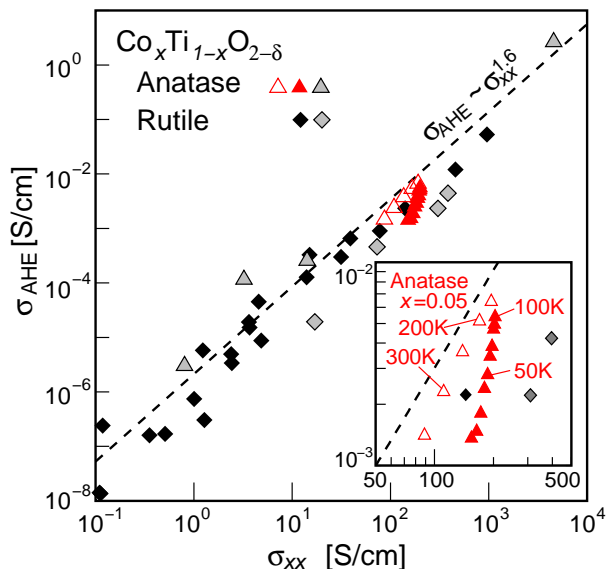


FIG. 4 Relationship between the anomalous Hall conductivity σ_{AHE} and conductivity σ_{xx} for anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ (triangles. this work and Refs.7-9) and rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ (diamonds. Refs.5 and 16). The solid gray symbols correspond to data taken from other groups. The inset shows a magnification around the data for anatase $\text{Ti}_{0.95}\text{Co}_{0.05}\text{O}_{2-\delta}$ in this work, where the open and solid triangles represent data for higher (≥ 150 K) and lower (≤ 100 K) temperatures.

the other hand, we reported that rutile phase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ has α of ~ 1.6 experimentally irrespective of temperature, x , and n .(5) The transport properties of anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ is qualitatively different from that of rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$: the former shows band conduction with large μ_{H} ($\sim 10 \text{ cm}^2/\text{Vs}$) similar to group III-V ferromagnetic semiconductors, while the latter shows hopping conduction with small μ_{H} ($\sim 0.1 \text{ cm}^2/\text{Vs}$) similar to typical transition metal oxides.

Relationship between σ_{xx} and σ_{AHE} for the anatase $\text{Ti}_{0.95}\text{Co}_{0.05}\text{O}_{2-\delta}$ film is shown in Fig. 4 by red triangles. Data for anatase ($\text{Ti}_{0.92}\text{Nb}_{0.03}\text{Co}_{0.05}\text{O}_2$ (Ref. 7), $\text{Ti}_{0.96}\text{Co}_x\text{Ni}_{0.04-x}\text{O}_{2-\delta}$ (Ref. 8) and $\text{Ti}_{0.0986}\text{Co}_{0.014}\text{O}_{2-\delta}$ (Ref. 9)) and rutile (Refs. 5, 16) phases from different research groups are also plotted for comparison. The data for anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ including the other reports fall into the same relationship as those for rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ with α of ~ 1.6 , irrespective of temperature, x , and n . This relationship seems to be universal for these $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ polymorphs in spite of the different transport properties as described above. Recent theory indicates that the exponent α depends on σ_{xx} and the amplitude of impurity potential.(11) The α of ~ 1.6 is reproduced in case of the weak impurity potential with $\sigma_{xx} \leq 10^3 \text{ S/cm}$ (dirty limit), while α is smaller than 1 for $\sigma_{xx} \geq 10^3 \text{ S/cm}$ (clean limit). The $\alpha \sim 1.6$ relationship has been experimentally reported also for transition metal oxides (TMOs) such as $\text{Nd}_2(\text{Mo}_{1-x}\text{Nb}_x)_2\text{O}_7$ and $\text{La}_{1-x}\text{Sr}_x\text{CoO}_3$. This result suggests that AHE of $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ is within a class of such metallic TMOs in spite of the broad range of their mobility.

In conclusion, the anomalous Hall effect of anatase $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ is shown to have almost the same magnetic field

dependence as magnetization, and to decrease with decreasing temperature in contrast with the temperature-independent magnetization. The anomalous Hall conductivity follows the unified relationship with the mobility, $\sigma_{\text{AHE}} \sim \mu_{\text{H}}^2$, suggesting significant role of the charge scattering on AHE. The scaling relationship between σ_{AHE} and σ_{xx} follows that of rutile $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ reported previously in spite of the different conduction mechanisms. The scaling exponent is explained by the recent theory and coincides with those of several transition metal oxides.

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